Description

N-channel Enhancement Mode Power MOSFET

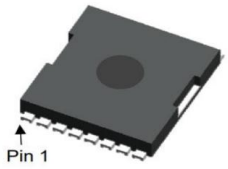
Features

- 40V, 250A
  $R_{DS(ON)}$ Typ =1mΩ @ V_{GS} = 10V
  $R_{DS(ON)}$ Typ =1.4mΩ @ V_{GS} = 4.5V
- Advanced Split Gate Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge

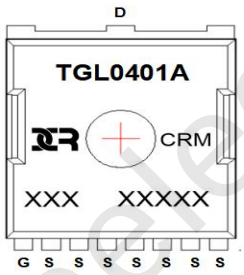
Applications

- Load Switch
- PWM Application
- Power Management

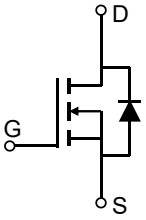
100% UIS TESTED!
100% ΔVds TESTED!



TOLL



Marking and Pin Assignment



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Outline	Package	Reel Size	Reel(pcs)	Per Carton (pcs)
CRMTGL0401A	CRMTGL0401A	TAPING	TOLL	13"	2000	10000

Absolute Maximum Ratings (@ T_J= 25°C unless otherwise specified)

Symbol	Parameter		Value	Units
V_{DS}	Drain-to-Source Voltage		40	V
V_{GS}	Gate-to-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C = 25°C	250	A
		T_C = 100°C	150	
I_{DM}	Pulsed Drain Current (1)		1000	A
E_{AS}	Single Pulsed Avalanche Energy (2)		506	mJ
P_D	Power Dissipation	T_C = 25°C	131	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		0.95	°C/W
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 150	°C

Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	40	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 40V, V_{GS} = 0V	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	1.2	1.65	2.5	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance(3)	V_{GS} = 10V, I_D = 20A	-	1.0	1.3	mΩ
		V_{GS} = 4.5V, I_D = 20A	-	1.4	1.8	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 20V, f = 1MHz	-	6050	-	pF
C_{oss}	Output Capacitance		-	2015	-	pF
C_{rss}	Reverse Transfer Capacitance		-	200	-	pF
Q_g	Total Gate Charge	V_{GS} = 0 to 10V, V_{DS} = 32V, I_D = 20A	-	99.8	-	nC
Q_{gs}	Gate Source Charge		-	52.1	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	11.2	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	V_{GS} = 10V, V_{DD} = 20V, I_D= 25A, R_{GEN} = 2Ω	-	19.2	-	ns
t_r	Turn-On Rise Time		-	106.8	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	214.3	-	ns
t_f	Turn-Off Fall Time		-	74.3	-	ns
Drain-Source Diode Characteristics and Max Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	250	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	1000	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_S = 30A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	I_F = 25A, di/dt = 100A/us	-	34.6	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	46	-	nC

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.

2. E_{AS} condition: Starting T_J=25C, V_{DD}=20V, V_G=10V, R_G=25ohm, L=0.5mH, I_{AS}=45A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%.

Test Circuit

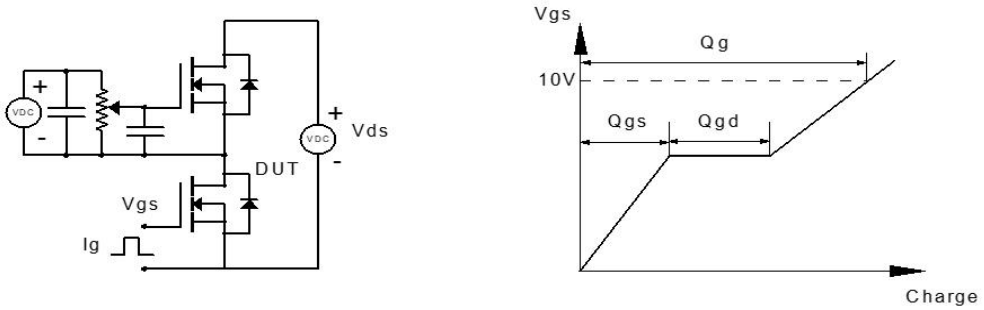


Figure 1: Gate Charge Test Circuit & Waveform

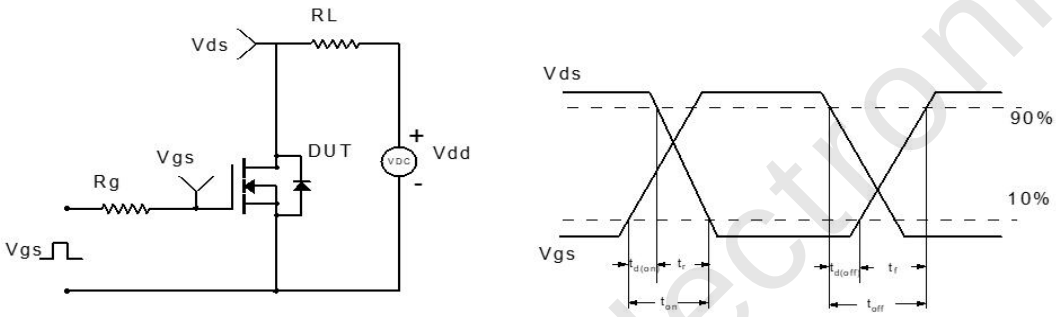


Figure 2: Resistive Switching Test Circuit & Waveform

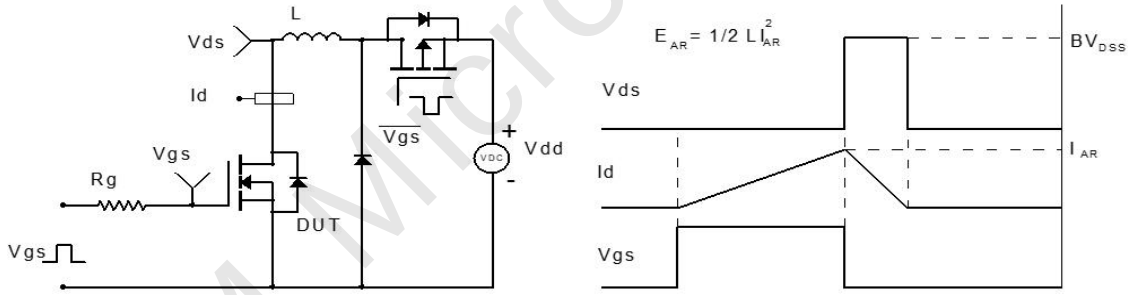


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

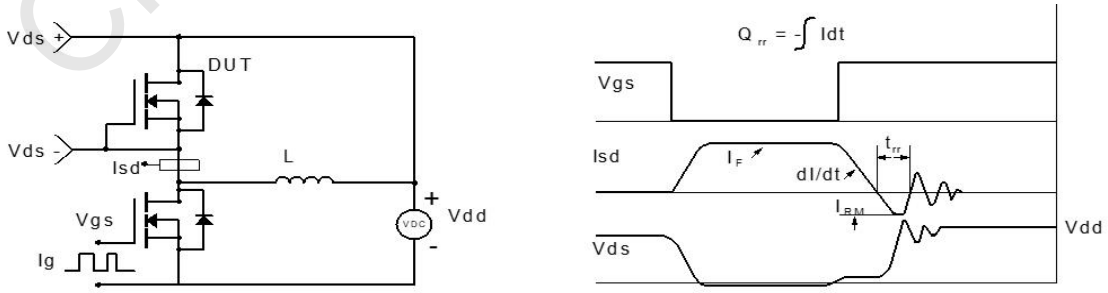
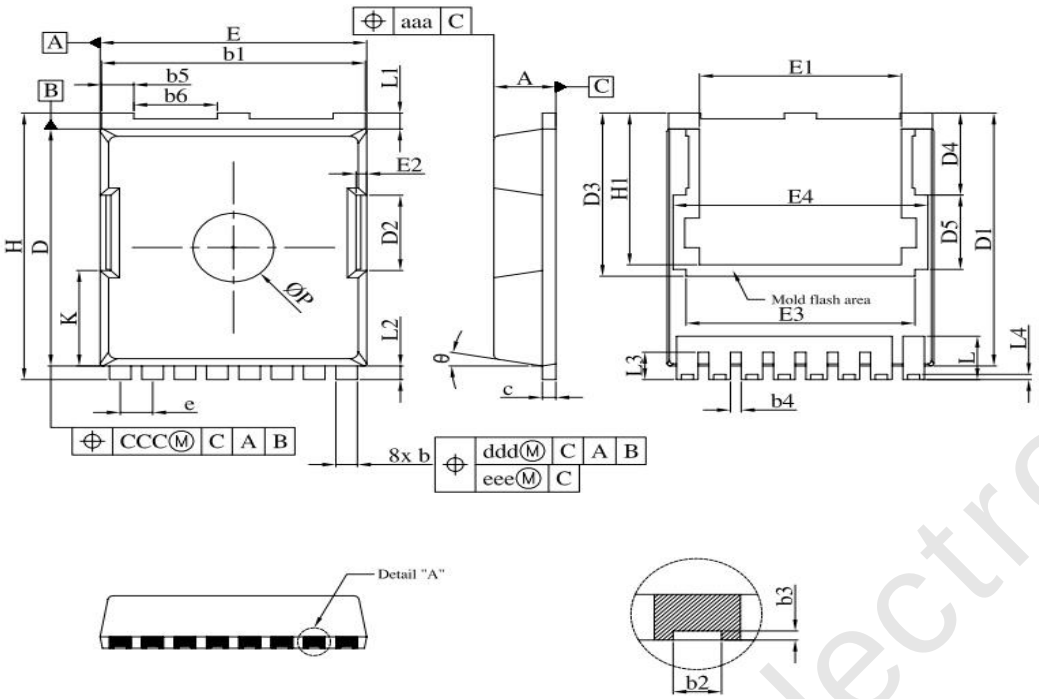


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(TOLL)



SYMBOL	COMMON		
	MILLIMETER		
	MIN.	NOMINAL	MAX.
A	2.20	2.30	2.40
b	0.70	0.80	0.90
b1	9.70	9.80	9.90
b2	0.36	0.45	0.55
b3	0.05	0.100	/
b4	0.30	0.40	0.50
b5	1.10	1.20	1.30
b6	3.00	3.10	3.20
c	0.40	0.50	0.60
D	10.28	10.38	10.55
D1	10.98	11.08	11.18
D2	3.20	3.30	3.40
D3		7.15	
D4		3.59	
D5		3.26	
e	1.10	1.20	1.30
E	9.80	9.90	10.00
E1	7.40	7.50	7.60
E2	0.30	0.40	0.50
E3		8.50	
E4		9.46	
H	11.50	11.68	11.85
H1	6.55	6.65	6.75
K	4.08	4.18	4.28
L	1.60	1.90	2.10
L1	0.50	0.70	0.90
L2	0.50	0.60	0.70
L3	1.00	1.20	1.30
L4	0.13	0.23	0.33
P	2.85	3.00	3.15
θ		10° REF	
aaa		0.20	
ccc		0.20	
ddd		0.25	
eee		0.20	